

**KSD5011**

**NPN TRIPLE DIFFUSED  
PLANAR SILICON TRANSISTOR**

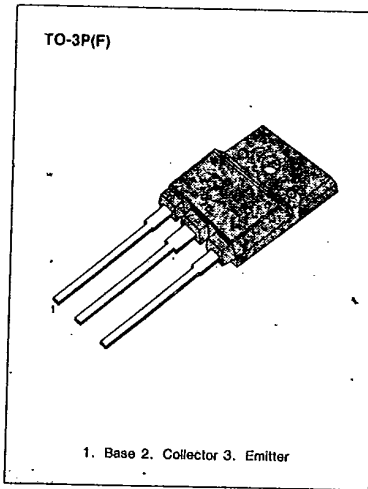
T-33-11

**COLOR TV HORIZONTAL OUTPUT  
APPLICATIONS (DAMPER DIODE BUILT IN)**

High Collector-Base Voltage  $V_{CBO}=1500V$

**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )**

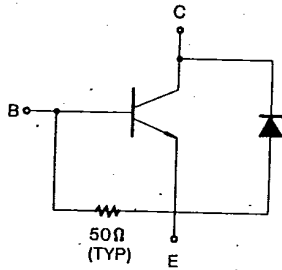
Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	1500	V
Collector-Emitter Voltage	$V_{CEO}$	800	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	3.5	A
Collector Current (Peak)	$I_C$	10	A
Collector Dissipation $T_C=25^\circ C$	$P_C$	50	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~150	$^\circ C$



3

**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )**

Characteristic	Symbol	Test Condition	Mjn	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=800V, I_E=0$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V, I_C=0$	40			
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=0.5A$	8		130	mA
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2.5A, I_B=0.8A$			8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2.5A, I_B=0.8A$			1.5	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=0.5A$		3		MHz
Damper Diode Turn On Voltage	$V_T$	$I_C=3.5A$			2	V
Fall Time	$t_f$	$I_C=3A, I_B1=0.8A$ $I_B2=-1.6A, V_{CC}=200V$ $RL=66.7\Omega$			0.4	$\mu S$

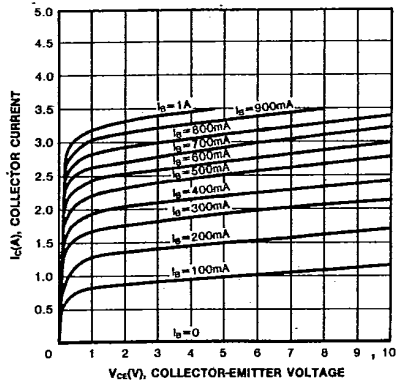


**NPN TRIPLE DIFFUSED  
PLANAR SILICON TRANSISTOR**

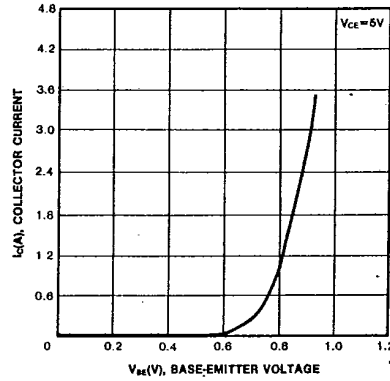
**KSD5011**

T-33-11

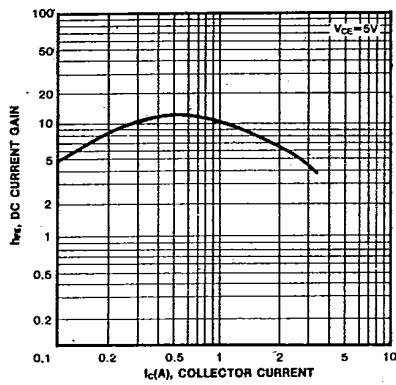
STATIC CHARACTERISTIC



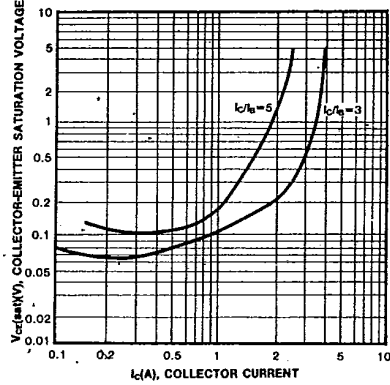
BASE-EMITTER ON VOLTAGE



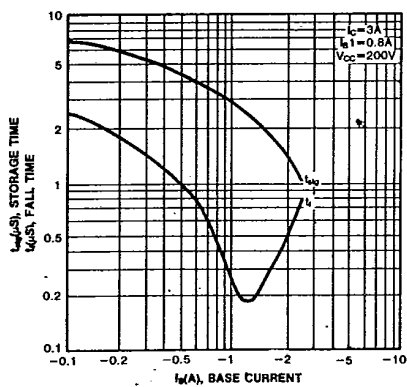
DC CURRENT GAIN



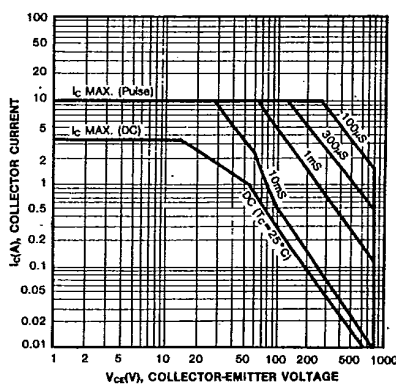
COLLECTOR-EMITTER SATURATION VOLTAGE



TURN ON TIME



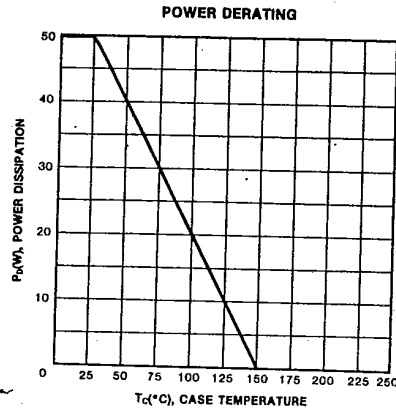
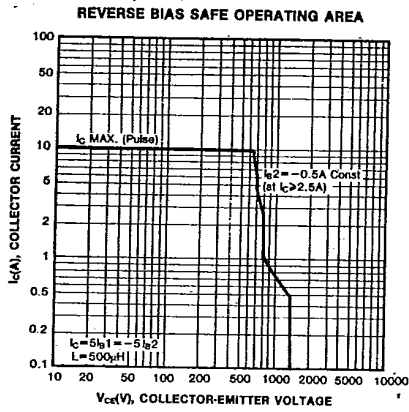
SAFE OPERATING AREA



KSD5011

NPN TRIPLE DIFFUSED  
PLANAR SILICON TRANSISTOR

T-33-11



3



**KSD5012**

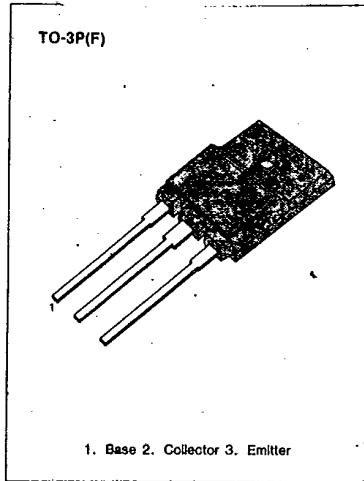
T-33-11

**COLOR TV HORIZONTAL OUTPUT  
 APPLICATIONS (DAMPER DIODE BUILT IN)**

High Collector-Base Voltage  $V_{CBO}=1500V$

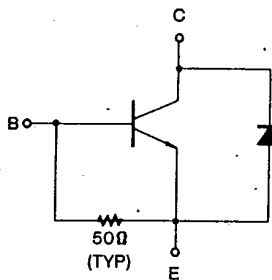
**ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	1500	V
Collector-Emitter Voltage	$V_{CEO}$	800	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	5	A
Collector Current (Peak)	$I_C$	16	A
Collector Dissipation ( $T_C=25^\circ C$ )	$P_C$	60	W
Junction Temperature	$T_J$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55~150	$^\circ C$



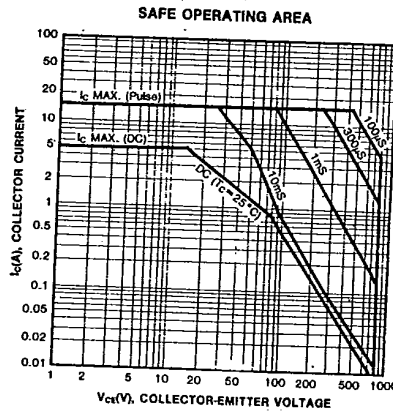
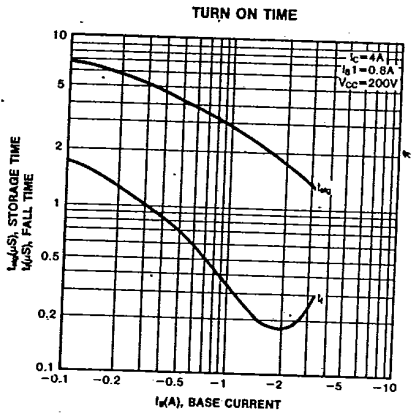
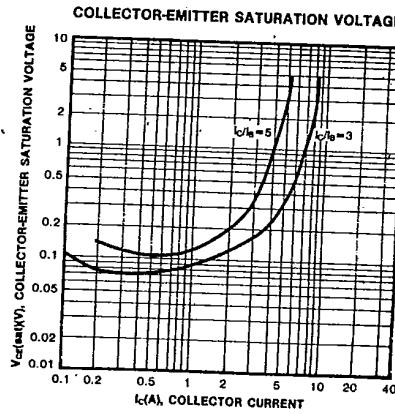
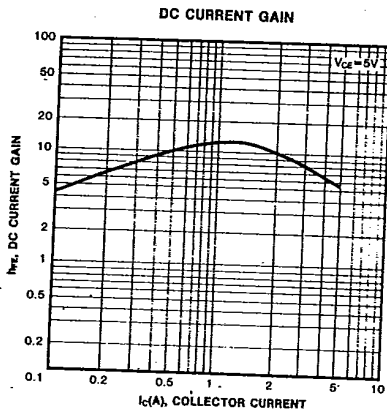
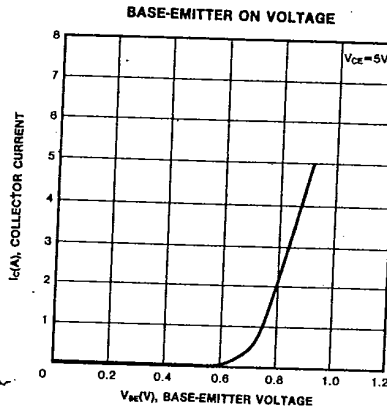
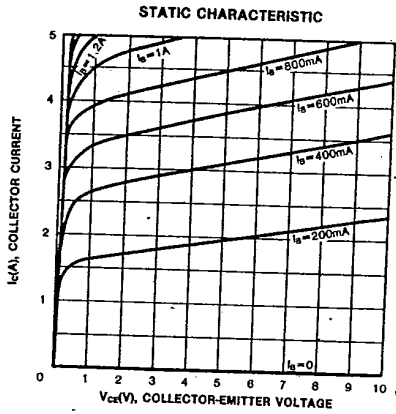
**ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=800V, I_E=0$			10	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V, I_C=0$	40		130	mA
DC Current Gain	$h_{FE}$	$V_{CE}=5V, I_C=1A$	8			
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.8A$			5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=0.8A$			1.5	V
Current Gain Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=1A$		3		MHz
Damper Diode Turn On Voltage	$V_f$	$I_f=5A$			2	V
Fall Time	$t_f$	$I_C=4A, I_{B1}=0.8A$ $I_{B2}=-1.6A, V_{CC}=200V$ $R_L=50\Omega$			0.4	$\mu S$



**KSD5012**

T-33-11



3

KSD5012

NPN TRIPLE DIFFUSED  
PLANAR SILICON TRANSISTOR

T-33-11

